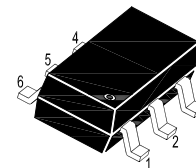
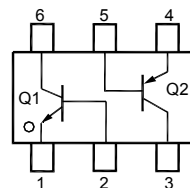


■ Dual Transistor (NPN+NPN)

■ Features

- Epitaxial planar die construction.
- Complementary Pair.
- Ultra-small surface mount package.
- One 2222A-Type NPN,
One 2907A-Type PNP.
- Ideal for low power amplification and switching



1. Collector 2. Base 3. Emitter
4. Emitter 5. Base 6. Collector

■ Simplified outline(SOT-363)

■ Absolute Maximum Ratings Ta = 25°C

● NPN 2222A

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	625	°C/W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

■ Absolute Maximum Ratings Ta = 25°C

● PNP 2907A

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-600	mA
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	625	°C/W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C
● NPN 2222A

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	75	-	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	40	-	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6	-	V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$ $V_{CB}=60V, I_E=0, T_A=150^\circ C$	-	10 10	nA μA
Collector cut-off current	I_{CEX}	$V_{CE}=60V, V_{EB(OFF)}=3.0V$	-	10	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0$	-	10	nA
Base cut-off current	I_{BL}	$V_{CE}=60V, V_{EB(OFF)}=3.0V$	-	20	nA
DC current gain	h_{FE}	$V_{CE}=10V, I_C=100\mu A$	35	-	
		$V_{CE}=10V, I_C=1.00mA$	50	-	
		$V_{CE}=10V, I_C=10mA$	75	-	
		$V_{CE}=10V, I_C=150mA$	100	300	
		$V_{CE}=10V, I_C=500mA$	40	-	
		$V_{CE}=10V, I_C=10mA, T_A=-55^\circ C$ $V_{CE}=1.0V, I_C=150mA,$	50 35	- -	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=150mA, I_B=15mA$ $I_C=500mA, I_B=50mA$	-	0.3 1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=150mA, I_B=15mA$ $I_C=500mA, I_B=50mA$	0.6 -	1.2 2.0	V
Transition frequency	f_T	$V_{CE}=20V, I_C=20mA, f=100MHz$	300	-	MHz
Output Capacitance	C_{obo}	$V_{CB}=10V, f=1.0MHz, I_E=0$	-	8	pF
Input Capacitance	C_{ibo}	$V_{EB}=0.5V, f=1.0MHz, I_C=0$	-	25	pF
Noise Figure	NF	$V_{CE}=10V, f=1.0kHz, I_C=0.1mA$ $R_g=1.0K\Omega,$	-	4.0	dB
Delay Time	t_d	$V_{CC}=30V, I_C=150mA,$	-	10	ns
Rise Time	t_r	$V_{BE(off)}=-0.5V, I_{B1}=15mA$	-	25	ns

■ Electrical Characteristics Ta = 25°C
● PNP 2907A

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A$ $I_E = 0$	-60	-	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA$ $I_B = 0$	-60	-	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A$ $I_C = 0$	-5	-	V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V$ $I_E = 0$ $V_{CB} = -50V$ $I_E = 0$ $T_A = 125^\circ C$	-	-10	nA μA
Collector cut-off current	I_{CEX}	$V_{CE} = -30V$ $V_{EB(OFF)} = -0.5V$	-	-50	nA
Base cut-off current	I_{BL}	$V_{CE} = -30V$ $V_{EB(OFF)} = -0.5V$	-	-50	nA
DC current gain	h_{FE}	$V_{CE} = -10V$ $I_C = -100\mu A$	75	-	
		$V_{CE} = -10V$ $I_C = -1mA$	100	-	
		$V_{CE} = -10V$ $I_C = -10mA$	100	-	
		$V_{CE} = -10V$ $I_C = -150mA$	100	300	
		$V_{CE} = -10V$ $I_C = -500mA$	50	-	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150mA$ $I_B = -15mA$ $I_C = -500mA$ $I_B = -50mA$	-	-0.4 -1.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -150mA$ $I_B = -15mA$ $I_C = -500mA$ $I_B = -50mA$	-	-1.3 -2.6	V
Transition frequency	f_T	$V_{CE} = -20V$, $I_C = -50mA$, $f = 100MHz$	200	-	MHz
Output Capacitance	C_{obo}	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$	-	-8.0	pF
Input Capacitance	C_{ibo}	$V_{EB} = -2.0V$, $f = 1.0MHz$, $I_C = 0$	-	30	pF
Turn-on time	t_{on}	$I_C = -150mA$, $V_{CC} = -30V$, $I_{B1} = -15mA$	-	45	ns
Delay Time	t_d	$V_{CC} = -30V$, $I_C = -150mA$, $I_{B1} = -15mA$	-	10	ns
Rise Time	t_r		-	40	ns

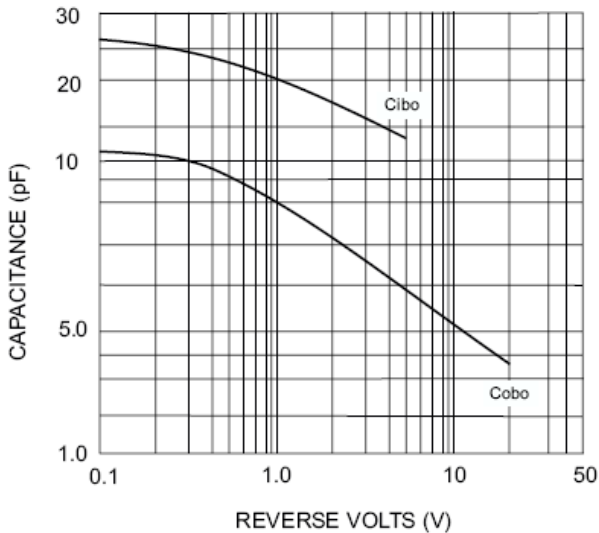


Fig. 1 (2222A) Capacitances (Typical)

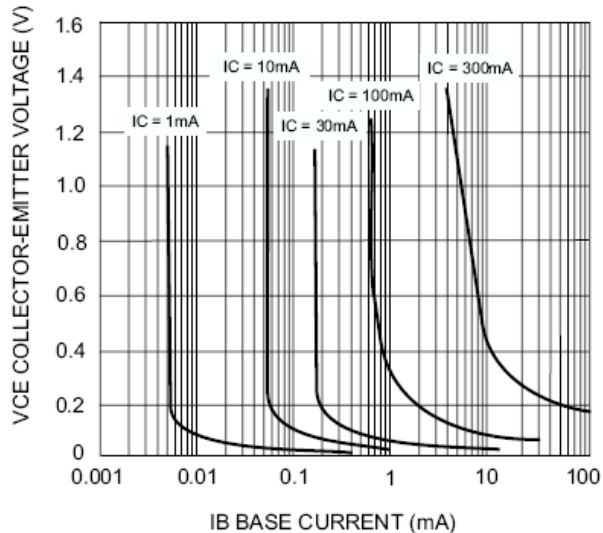


Fig. 4 (2907A) Typical Collector Saturation Region

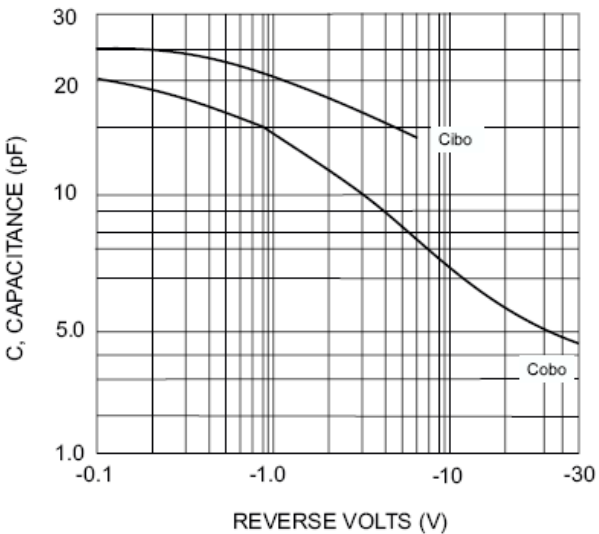


Fig. 3 (2907A) Capacitances (Typical)

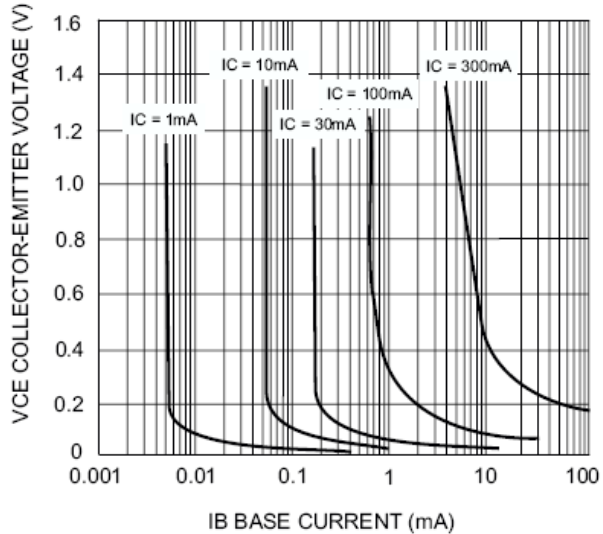
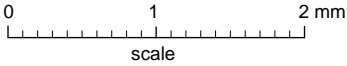
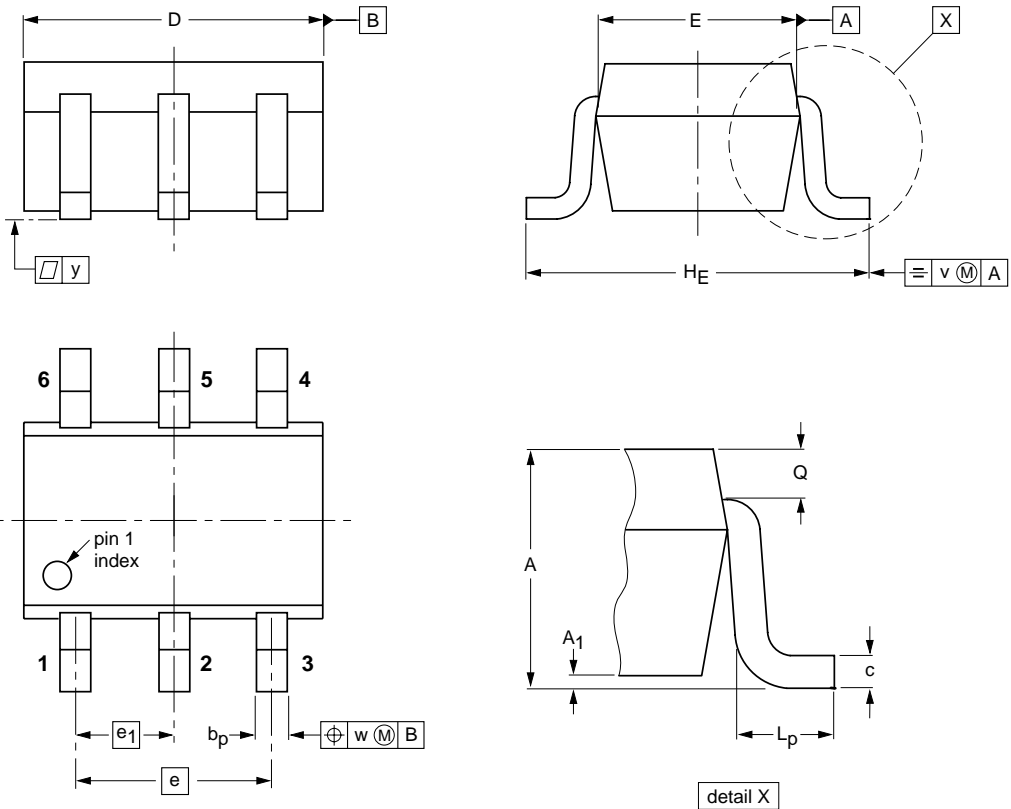


Fig. 4 (2907A) Typical Collector Saturation Region

■ SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [SLKORMICRO manufacturer](#):

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N4403](#) [2N6728](#)
[2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-](#)
[TL-E](#) [MCH4021-TL-E](#) [Jantx2N5416](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [UMX21NTR](#) [MCH6102-TL-E](#)
[TTA1452B,S4X\(S](#) [2N3879](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANTX2N3735](#) [JANSR2N2222AUB](#)
[CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#)
[MMDT3946FL3-7](#) [2N4240](#) [JANS2N3019](#) [MSB30KH-13](#) [2N2221AUB](#)